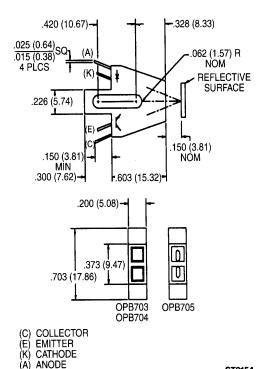


REFLECTIVE OBJECT SENSORS

OPB703/OPB704/OPB705

PACKAGE DIMENSIONS



ST2154

NOTES:

- 1. CATHODE AND EMITTER LEADS ARE .050" NOM SHORTER THAN
- ANODE AND COLLECTOR LEADS.
- 2. DIMENSIONS ARE IN INCHES (mm).
- TOLERANCE IS ±.010 (.25) З.
- UNLESS OTHERWISE SPECIFIED.

OPB703 - IR TRANSPARENT DUST COVER **OPB704 - IR TRANSPARENT DUST COVER OPB705 - OFFSET LENS**

DESCRIPTION

The OPB703, OPB704, and OPB705 consist of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter.



- Phototransistor output.
- High Sensitivity.
- Low cost plastic housing.
- OPB703/OPB704, dust cover; lens.
- OPB705, offset lens.



REFLECTIVE OBJECT SENSOR

SEMICONDUCTOR

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless Otherw	
Storage Temperature Operating Temperature Soldering:	
Lead Temperature (Iron) Lead Temperature (Flow)	
INPUT DIODE Continuous Forward Current Reverse Voltage Power Dissipation	
OUTPUT TRANSISTOR Collector-Emitter Voltage Emitter-Collector Voltage Collector Current Power Dissipation	

PARAMETER	SYMBOL	MIN.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE					
Forward Voltage	VF		1.70	V	$I_F = 40 \text{ mA}$
Reverse Leakage Current	I _R	_	100	μΑ	$V_{R} = 2.0 V$
OUTPUT TRANSISTOR					
Emitter-Collector Breakdown	BVECO	5		V	$l_{e} = 100 \ \mu A, Ee = 0$
Collector-Emitter Breakdown	BV _{CEO}	30		V	$I_{c} = 100 \ \mu A, Ee = 0$
Collector-Emitter Leakage	I _{CEO}	_	100	nA	$V_{ce} = 10.0 V, Ee = 0$
COUPLED					
On-State Collector Current					
OPB703		200		μA	$I_{\rm F}=40$ mA, $V_{\rm CE}=5$ V, $D=.150''$ (5.6
OPB704	C(ON)	200		μA	$l_{\rm F} = 40 \text{ mA}, V_{\rm CE} = 5 \text{ V}, D = .150^{\prime\prime} {}^{\rm (5.6)}$
OPB705	I _{C(ON)}	100		μA	$l_{\scriptscriptstyle F}=$ 40 mA, $V_{\scriptscriptstyle CE}=$ 5 V, D = .150" $^{\scriptscriptstyle (5,6)}$
Crosstalk	I _{cx}		20	μA	$I_{\rm F} = 40$ mA, $V_{\rm CE} = 5V^{(7)}$

NOTES

1. Derate power dissipation linearly 1.67 mW/°C above 25°C.

- Derate power dissipation linearly 1.67 mW/ C above 25 C.
 RMA flux is recommended.
 Rethanol or Isopropyl alcohols are recommended as cleaning agents.
 Soldering iron tip ¼e" (1.6 mm) from housing.
 D is the distance from the assembly face to the reflective surface.
 Measured using Eastman Kodak neutral test card with 90% diffused reflecting surface.
 Cross talk is the photocurrent measured with current to the input diode and no reflective surface.



REFLECTIVE OBJECT SENSOR

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- A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.